UMSB Plastic-Encapsulate Bridge Rectifier

Fast Recovery Bridge Rectifier

Features

- $I_{F(AV)}$ 4A
- V_{RRM} 1000V
- High surge current capability
- Glass passivated chip

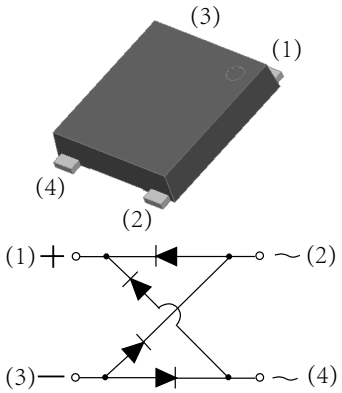
Applications

- General purpose 1 phase Bridge rectifier applications

Marking

- RMSB40M

UMSB



Limiting Values (Absolute Maximum Rating)

Item	Symbol	Unit	Conditions		RMSB40M
Repetitive Peak Reverse Voltage	V_{RRM}	V			1000
Maximum RMS Voltage	V_{RMS}	V			700
Maximum DC Blocking Voltage	V_{DC}	V			1000
Average Rectified Output Current	I_O	A	60Hz sine wave, R-load,Ta=110℃	On alumina substrate	4.0
Surge(Non-repetitive)Forward Current	I_{FSM}	A	8.3ms sine wave, 1 cycle, T_j=25℃		100
Current Squared Time	I^2t	A^2S	1ms≤t<8.3ms Tj=25℃， Rating of per diode		41.5
Operation Junction and Storage Temperature Range	T_J,T_{stg}	℃			-55 ~+150

Electrical Characteristics (T=25℃ Unless otherwise specified)

Item	Symbol	Unit	Test Condition		Max
Maximum Peak Forward Voltage	V_{FM}	V	I_{FM}=4.0A, Pulse measurement, Rating of per diode		1.3
Maximum Reverse Recovery Time	T_{RR}	ns	Measured with IF=0.5A,IR=1A,IRR=0.25A		500
Maximum Peak Reverse Current	I_{RRM1}	μA	V_{RM}=V_{RRM} , Pulse measurement, Rating of per diode	T_A=25℃	5.0
	I_{RRM2}	μA		T_A=125℃	500
Thermal Resistance	$R_{\theta J-A}$	℃/W	Between junction and ambient, On alumina substrate		55
	$R_{\theta J-L}$		Between junction and lead		15
	$R_{\theta J-C}$		Between junction and case		10

Typical Characteristics

FIG.1: FORWARD CURRENT DERATING CURVE

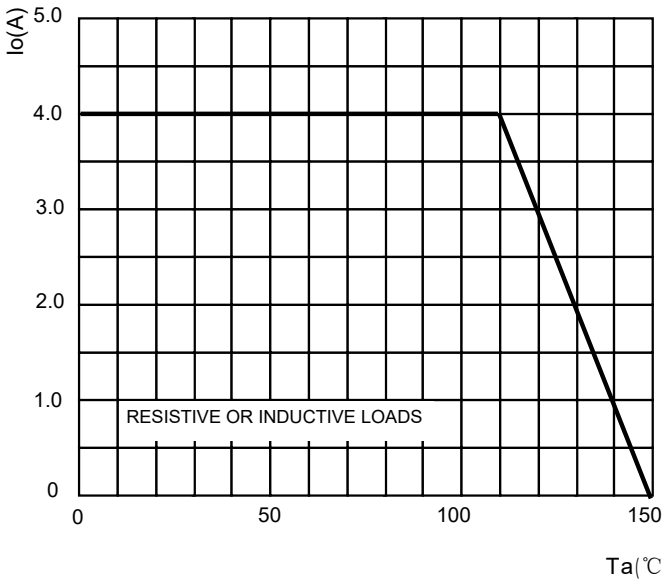


FIG.2: MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

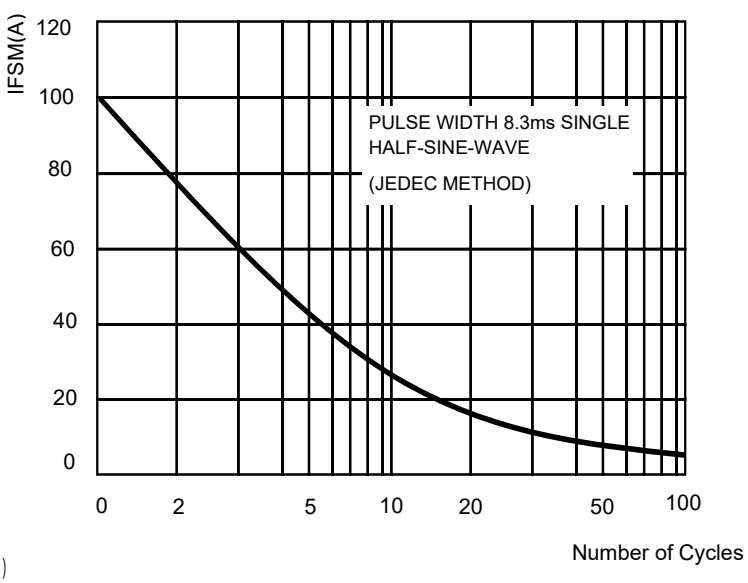


FIG.3: TYPICAL FORWARD CHARACTERISTICS

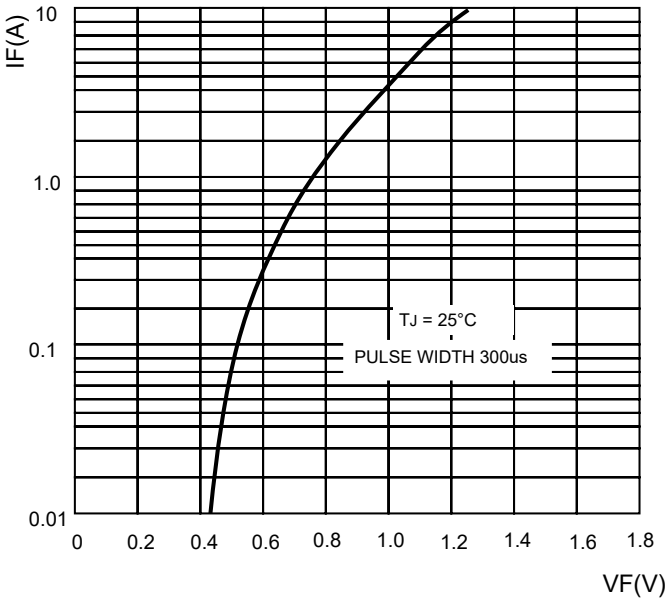
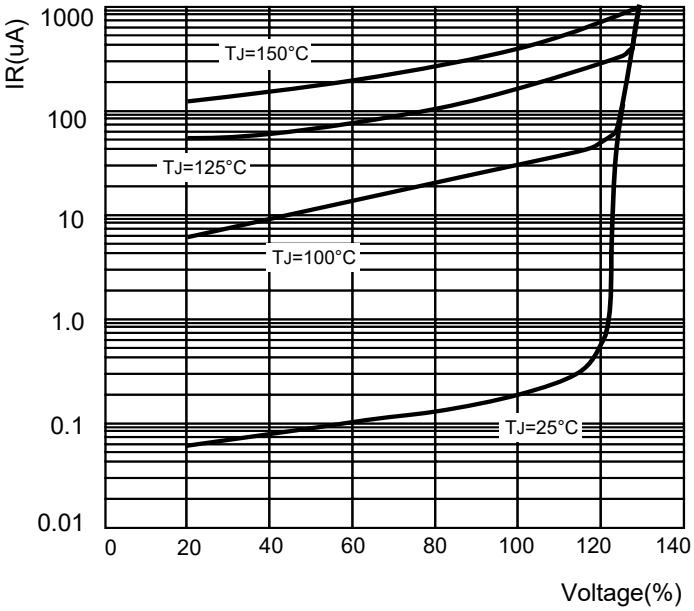
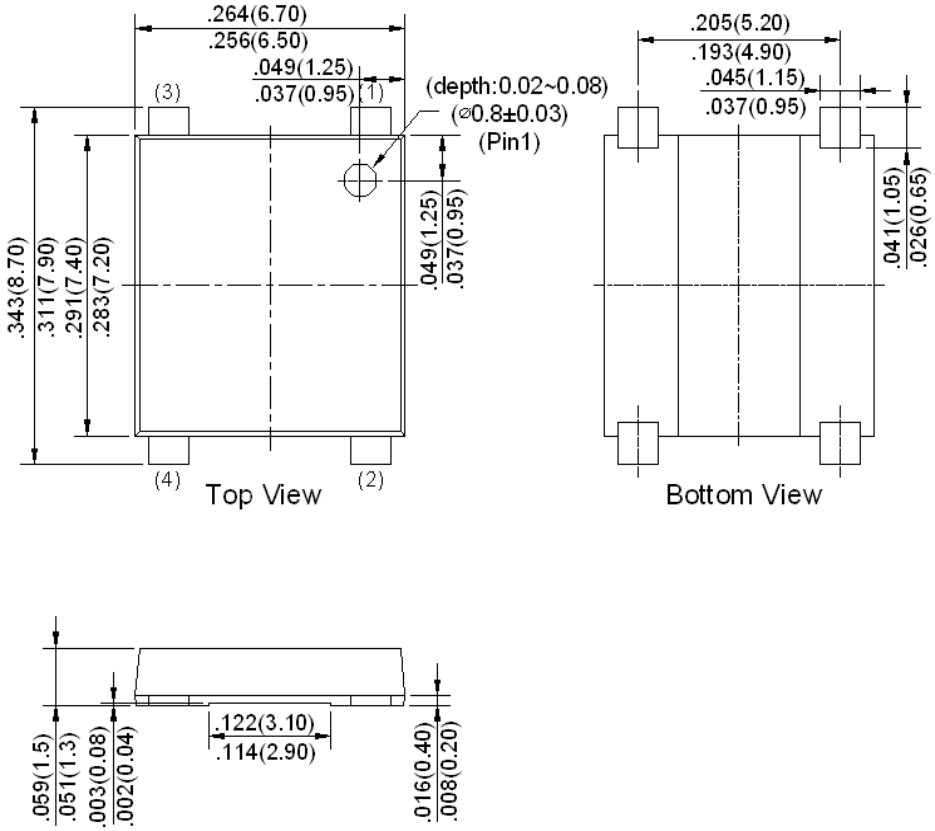


FIG.4:TYPICAL REVERSE CHARACTERISTICS

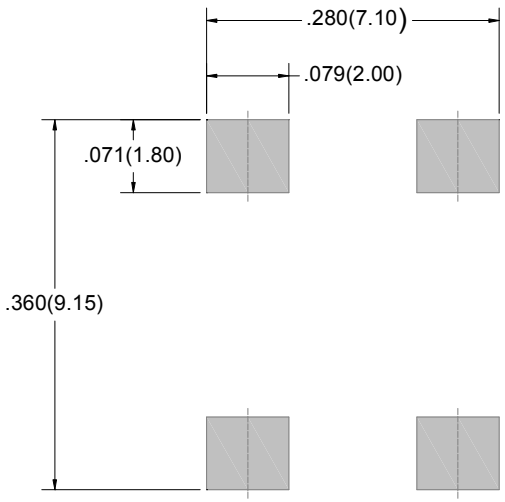


UMSB Package Outline Dimensions



Dimensions in inches and (millimeters)

UMSB Suggested Pad Layout



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:± 0.05mm.
3.The pad layout is for reference purposes only.